

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listings of Claims:

1. (currently amended) A method of fabricating a semiconductor chip package comprising ~~the steps of:~~

providing a semiconductor wafer, said semiconductor wafer having a top surface and a bottom surface, a plurality of bonding pads being located on said top surface;

applying at least one a layer of nonconductive epoxy sublayer to a said bottom surface of said semiconductor wafer using a screen printing process;

curing said at least one nonconductive epoxy sublayer;

applying a final nonconductive epoxy sublayer on top of said at least one epoxy sublayer, said at least one nonconductive epoxy sublayer and said final nonconductive epoxy sublayer together forming a nonconductive epoxy layer;

partially curing said final nonconductive epoxy sublayer such that said final epoxy sublayer is in a soft but solid form;

while said final nonconductive epoxy sublayer is still only partially cured, sawing said wafer to create a plurality of semiconductor dice, said nonconductive epoxy layer completely covering a bottom surface of each of said semiconductor dice; and

attaching at least one of said semiconductor dice to a die-attach member pad by means of said epoxy layer.

2. (currently amended) The method of Claim 1 further comprising wire-bonding said die-attach member to at least one of said bonding pads ~~wherein applying said epoxy layer comprises applying at least two epoxy sublayers.~~

3. (currently amended) The method of Claim 1 2 wherein said die-attach member comprises a pad comprising hard-curing a first epoxy sublayer before forming a second epoxy sublayer.

4. (currently amended) The method of Claim 1 wherein said die-attach member comprises 2 comprising partially curing a final epoxy sublayer before bringing said final epoxy sublayer into contact with a leadframe.

5. (currently amended) The method of Claim 1 ~~Claim 4~~ wherein partially curing said final nonconductive epoxy sublayer comprises heating said final epoxy sublayer until it is in a soft solid state.

6. (currently amended) The method of Claim 5 ~~Claim 4~~ wherein partially curing said final nonconductive epoxy sublayer comprises heating said final epoxy sublayer to a temperature in the range of 100° C for a ~~time~~ duration of 60 seconds.

7. (currently amended) The method of Claim 5 ~~Claim 4~~ wherein attaching at least one of said dice to a die-attach member pad comprises heating ~~heating~~ said final nonconductive epoxy sublayer ~~to a temperature in the range of 110° C to 170° C for a time duration of 50 to 400 seconds.~~

8. (currently amended) The method of Claim 7 wherein attaching at least one of said dice to a die-attach member pad comprises heating said final nonconductive epoxy sublayer to a temperature in the range of 110° C to 170° C for a duration of 50 to 400 seconds ~~pressing said at least one die against said pad with a force in the range of 100 to 350 grams.~~

9. (currently amended) The method of Claim 1 ~~Claim 4~~ wherein applying at least one nonconductive epoxy sublayer ~~said epoxy layer~~ comprises applying only one ~~two~~ epoxy sublayer ~~sublayers~~.

10. (currently amended) The method of Claim 1 ~~Claim 9~~ wherein said die-attach member comprises a split die-attach pad ~~comprising hard curing a first epoxy sublayer before forming a second epoxy sublayer and partially curing said second epoxy layer before bringing said second epoxy sublayer into contact with a leadframe.~~

11. (new) The method of Claim 1 wherein said die-attach member comprises a plurality of contacts for a no-lead package.

12. (new) The method of Claim 11 comprising wire-bonding at least one of said contacts for a no-lead package to at least one of said bonding pads.

13. (new) The method of Claim 1 further comprising
- providing a second semiconductor wafer, said second semiconductor wafer having a top surface and a bottom surface, a plurality of bonding pads being located on said top surface of said second semiconductor wafer;
 - applying at least one nonconductive adhesive sublayer to said bottom surface of said second semiconductor wafer using a screen printing process;
 - curing said at least one nonconductive adhesive sublayer;
 - applying a final nonconductive adhesive sublayer on top of said at least one adhesive sublayer, said at least one nonconductive adhesive sublayer and said final nonconductive adhesive sublayer together forming a nonconductive adhesive layer;
 - partially curing said final nonconductive adhesive sublayer such that said final nonconductive adhesive sublayer is in a soft but solid form;
 - while said final nonconductive adhesive sublayer is still only partially cured, sawing said second semiconductor wafer to create a second plurality of semiconductor dice, said nonconductive adhesive layer completely covering a bottom surface of each of said second plurality of semiconductor dice; and
 - attaching at least one of said second plurality of semiconductor dice to one of said plurality of semiconductor dice by means of said nonconductive adhesive layer.

14. (new) The method of Claim 1 comprising attaching a sawing tape to said epoxy layer before sawing said semiconductor wafer.

15. (new) The method of Claim 14 wherein sawing said semiconductor wafer comprises sawing said semiconductor wafer from said top surface of said wafer, said sawing creating a cut that extends partially through said sawing tape.

16. (new) A method of fabricating a semiconductor chip package comprising:
- providing a semiconductor wafer;

depositing in succession a plurality of nonconductive epoxy layers on a first surface of said wafer, said plurality of nonconductive epoxy layers comprising a top epoxy layer;

curing each of said epoxy layers except for said top epoxy layer;

partially curing said top epoxy layer;

sawing said wafer into a plurality of dice, a first surface of each of said dice being completely covered by said nonconductive epoxy layers;

pressing the top epoxy layer on one of said dice against a pad or leadframe;

and

applying heat to said pad or leadframe to completely cure said top epoxy layer on said one of said dice.

17. (new) The method of Claim 16 wherein pressing the top epoxy layer on one of said dice against a pad or leadframe and applying heat to said pad or leadframe to completely cure said top epoxy layer on said one of said dice comprises pressing the top epoxy layer on said one of said dice against a pad or leadframe with a force in the range of 100 to 350 grams while heating said pad or leadframe to a temperature in the range of 110° C to 170° C for a duration of 50 to 400 seconds.